

## BAT54J/W/AW/CW/SW

### SMALL SIGNAL SCHOTTKY DIODE

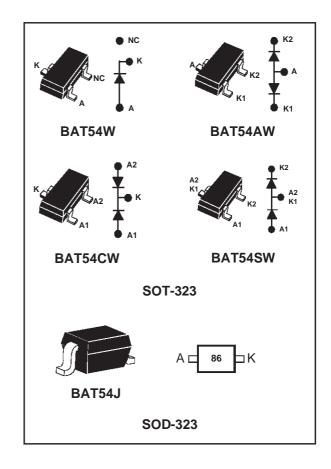
#### **FEATURES AND BENEFITS**

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNT DEVICE

#### **DESCRIPTION**

Schottky barrier diodes encapsulated either in SOT-323 or SOD-323 small SMD packages.

Single and double diodes with different pining are available.



#### **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage	30	V	
I <sub>F</sub>	Continuous forward current	0.3	Α	
I <sub>FSM</sub>	Surge non repetitive forward current	tp=10ms sinusoidal	1	Α
P <sub>tot</sub>	Power dissipation (note 1) SOD-323 Tamb = 25°C SOT-323		230	mW
			]	
T <sub>stg</sub>	Maximum storage temperature range	- 65 to +150	°C	
Tj	Maximum operating junction temperature *	150	°C	
TL	Maximum temperature for soldering during	260	°C	

Note 1: for double diodes, Ptot is the total dissipation of both diodes

\* :  $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$  thermal runaway condition for a diode on its own heatsink

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#### THERMAL RESISTANCE

Symbol	Parameters		Value	Unit
R <sub>th (j-a)</sub>	Junction to ambient (*)	SOD-323	550	°C/W
		SOT-323		°C/W

<sup>(\*)</sup> Mounted on epoxy board, with recommended pad layout.

#### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameters	Tests conditions		Min.	Тур.	Max.	Unit
V <sub>F</sub> *	Forward voltage drop	Tj = 25°C	I <sub>F</sub> = 0.1 mA			240	mV
			I <sub>F</sub> = 1 mA			320	
			IF = 10 mA			400	
			I <sub>F</sub> = 30 mA			500	
			I <sub>F</sub> = 100 mA			900	
I <sub>R</sub> **	Reverse leakage current	Tj = 25°C	V <sub>R</sub> = 30 V			1	μА
		Tj = 100°C				100	

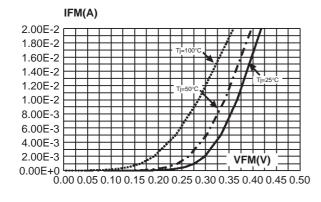
Pulse test :  $^*$  tp = 380  $\mu$ s,  $\delta$  < 2%  $^{**}$  tp = 5 ms,  $\delta$  < 2%

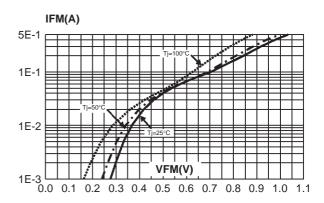
#### **DYNAMIC CHARACTERISTICS** (Tj = 25 °C)

Symbol	Parameters	Tests conditions	Min.	Тур.	Max.	Unit
С	Junction capacitance	Tj = 25°C V <sub>R</sub> = 1 V F = 1 MHz			10	pF
t <sub>rr</sub>	Reverse recovery time	$I_F = 10 \text{ mA}  I_R = 10 \text{ mA}  Tj = 25^{\circ}\text{C}$ $I_{rr} = 1 \text{ mA}  R_L = 100 \Omega$			5	ns

**Fig. 1-1:** Forward voltage drop versus forward current (typical values, low level).

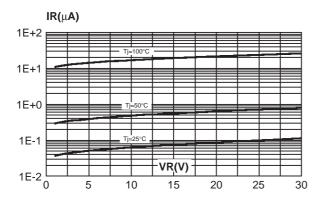
**Fig. 1-2:** Forward voltage drop versus forward current (typical values, high level).





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Fig. 2: Reverse leakage current versus reverse voltage applied (typical values).



**Fig. 4:** Junction capacitance versus reverse voltage applied (typical values).

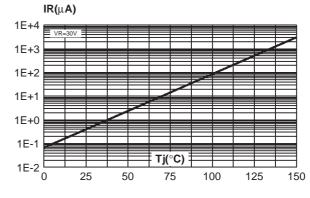
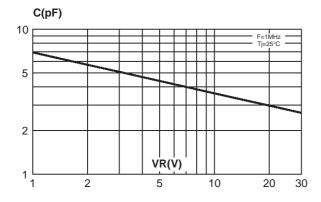


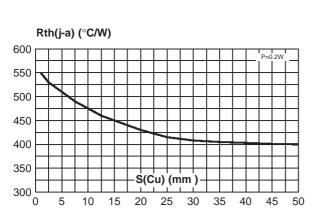
Fig. 3: Reverse leakage current versus junction

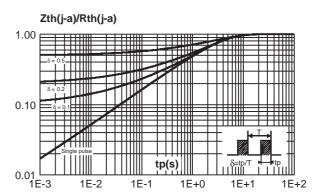
temperature.

**Fig. 5:** Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy FR4 with recommended pad layout,  $e(Cu)=35\mu m$ )



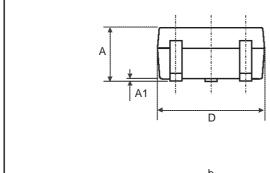
**Fig. 6:** Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35µm.)

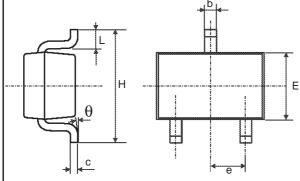




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# **PACKAGE MECHANICAL DATA** SOT-323



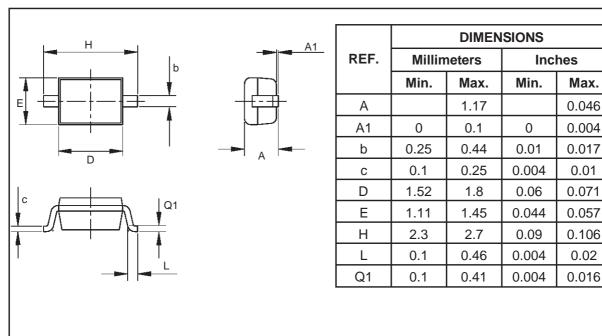


	DIMENSIONS					
REF.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.8		1.1	0.031		0.043
A1	0.0		0.1	0.0		0.004
b	0.25		0.4	0.010		0.016
С	0.1		0.26	0.004		0.010
D	1.8	2.0	2.2	0.071	0.079	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65			0.026	
Н	1.8	2.1	2.4	0.071	0.083	0.094
L	0.1	0.2	0.3	0.004	0.008	0.012
θ	0		30°	0		30°

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#### **PACKAGE MECHANICAL DATA**

SOD-323



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BAT54W	D73	SOT-323	0.006g	3000	Tape & reel
BAT54AW	D74	SOT-323	0.006g	3000	Tape & reel
BAT54CW	D77	SOT-323	0.006g	3000	Tape & reel
BAT54SW	D78	SOT-323	0.006g	3000	Tape & reel
BAT54J	86	SOD-323	0.005g	3000	Tape & reel

■ Epoxy meets UL94,V0

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